

# **PNP General Purpose Amplifier**

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 800 mA. Sourced from Process 79.

## Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	1.0	А
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations. 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

# Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units
		TN6729A	*NZT6729	
P <sub>D</sub>	Total Device Dissipation	1.0	1.0	W
	Derate above 25°C	8.0	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	125	°C/W

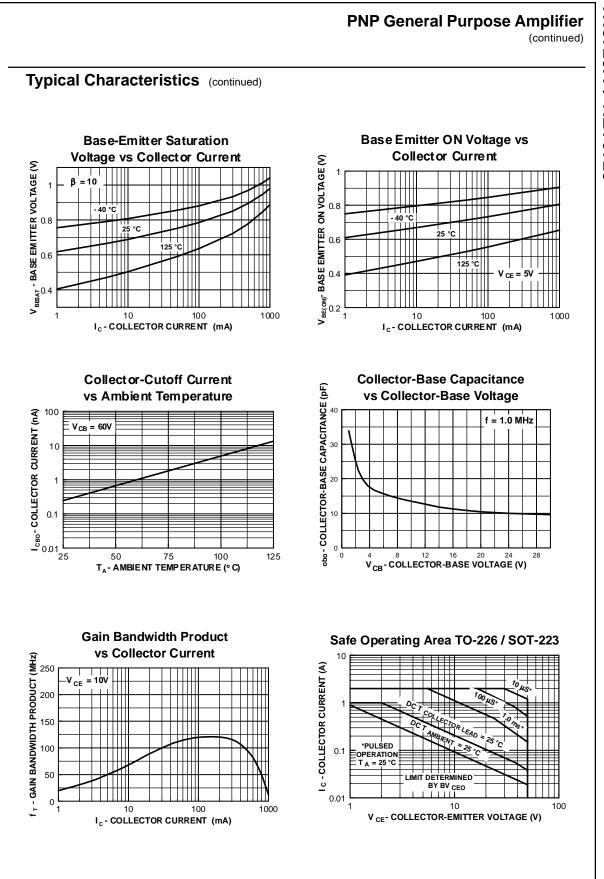
\*Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

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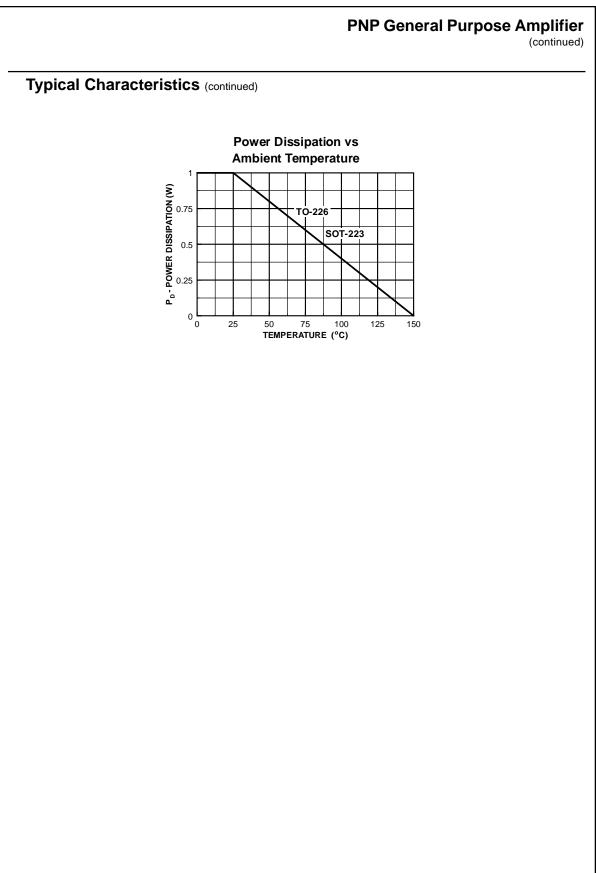
# PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Unit
OFF CHAI	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	80		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{E} = 0$	80		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 1.0 \text{ mA}, I_{\rm C} = 0$	5.0		V
СВО	Collector-Cutoff Current	$V_{CB} = 60 \text{ V}, \text{ I}_{E} = 0$		0.1	μA
EBO	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		10	μΑ
ON CHAR	ACTERISTICS*				
η <sub>FE</sub>	DC Current Gain	$      I_{C} = 50 \text{ mA}, V_{CE} = 1.0 \text{ V} \\       I_{C} = 250 \text{ mA}, V_{CE} = 1.0 \text{ V} \\       I_{C} = 500 \text{ mA}, V_{CE} = 1.0 \text{ V} $	80 50 20	250	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 250 \text{ mA}, I_{\rm B} = 10 \text{ mA}$		0.5	V
	Base-Emitter On Voltage	$I_{\rm C} = 250 \text{ mA}, I_{\rm B} = 25 \text{ mA}$ $I_{\rm C} = 250 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$		0.35	V
/ <sub>BE(on)</sub>	Dase-Linitlei On Voltage	$1_{\rm C} = 230$ mA, $V_{\rm CE} = 1.0$ V		1.2	v
SMALL SI	GNAL CHARACTERISTICS				
Դ <sub>fe</sub>	Small-Signal Current Gain	$I_{C} = 200 \text{ mA}, V_{CE} = 5.0 \text{ V},$	2.5	25	
Ite		f = 20 MHz			
*Pulse Test: P	Collector-Base Capacitance Pulse Width $\leq$ 300 $\mu$ s, Duty Cycle $\leq$ 1.0% ages (V) and currents (A) are negative polarity for PNP	$\begin{array}{c} f=20 \text{ MHz} \\ \hline V_{CB}=10 \text{ V}, \text{ I}_{E}=0, \text{ f}=1.0 \text{ MHz} \end{array}$ transistors.		30	pF
*Pulse Test: P NOTE: All volt:	ulse Width $\leq$ 300 $\mu$ s, Duty Cycle $\leq$ 1.0%	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		30	pF
*Pulse Test: P NOTE: All volt	Pulse Width $\leq$ 300 $\mu$ s, Duty Cycle $\leq$ 1.0% ages (V) and currents (A) are negative polarity for PNP	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz	Emitter S		
C <sub>cb</sub> *Pulse Test: P NOTE: All volt: Typica	Pulse Width $\leq$ 300 $\mu$ s, Duty Cycle $\leq$ 1.0% ages (V) and currents (A) are negative polarity for PNP al Characteristics	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz transistors.		Saturatio	n
C <sub>cb</sub> *Pulse Test: P NOTE: All volt: Typica	Pulse Width ≤ 300 µs, Duty Cycle ≤ 1.0% ages (V) and currents (A) are negative polarity for PNP al Characteristics Fypical Pulsed Current Gain vs Collector Current	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz transistors.		Saturatio	n
*Pulse Test: P NOTE: All volt	Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0% ages (V) and currents (A) are negative polarity for PNP al Characteristics Γγpical Pulsed Current Gain	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz transistors.		Saturatio	n
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*Pulse Test: P NOTE: All volt	Pulse Width $\leq$ 300 µs, Duty Cycle $\leq$ 1.0% ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current 125 °C	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz transistors.		Saturatio or Currer	n
	Pulse Width $\leq$ 300 µs, Duty Cycle $\leq$ 1.0% ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current 125 °C	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ transistors.  Collector-I Voltage vs 1 $\beta = 10$ $\beta = 10$		Saturatio or Currer	n

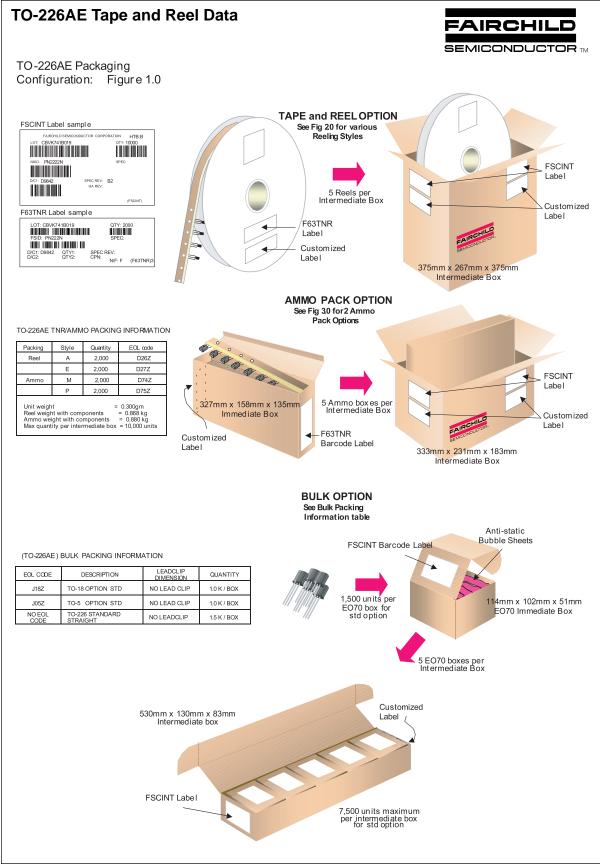
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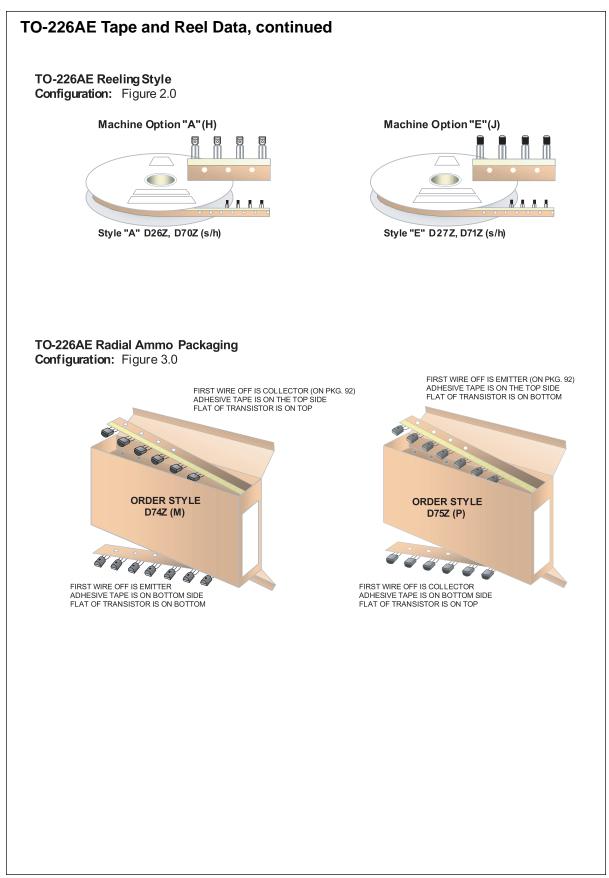


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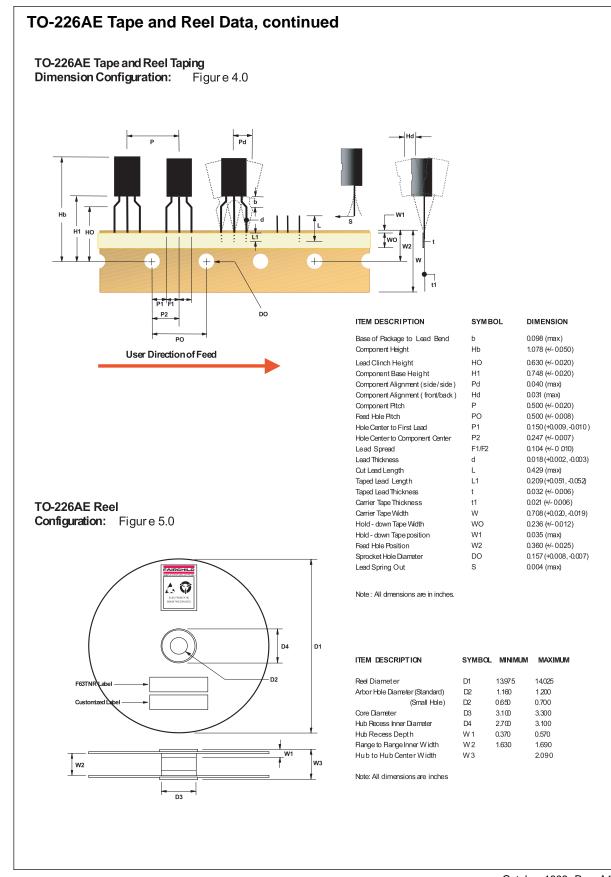


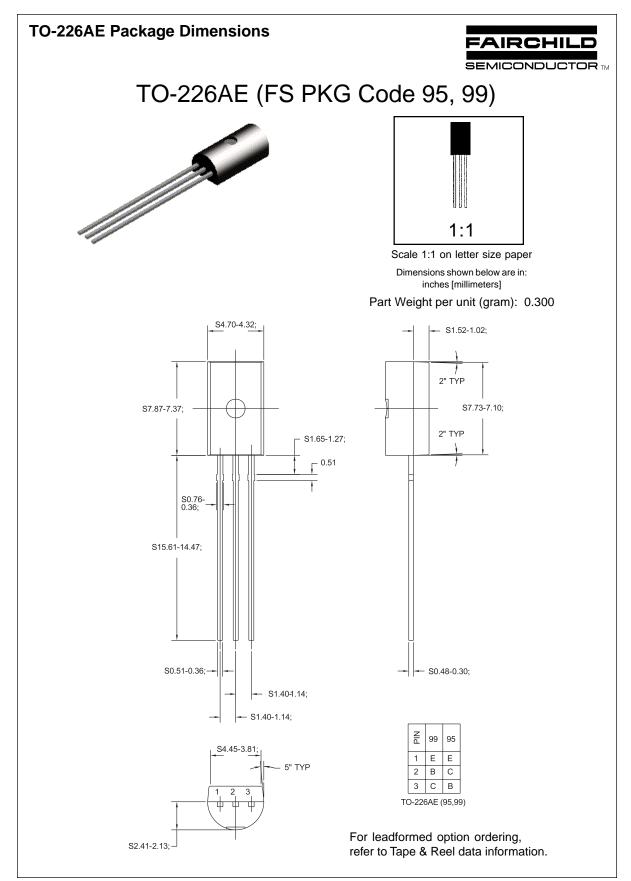
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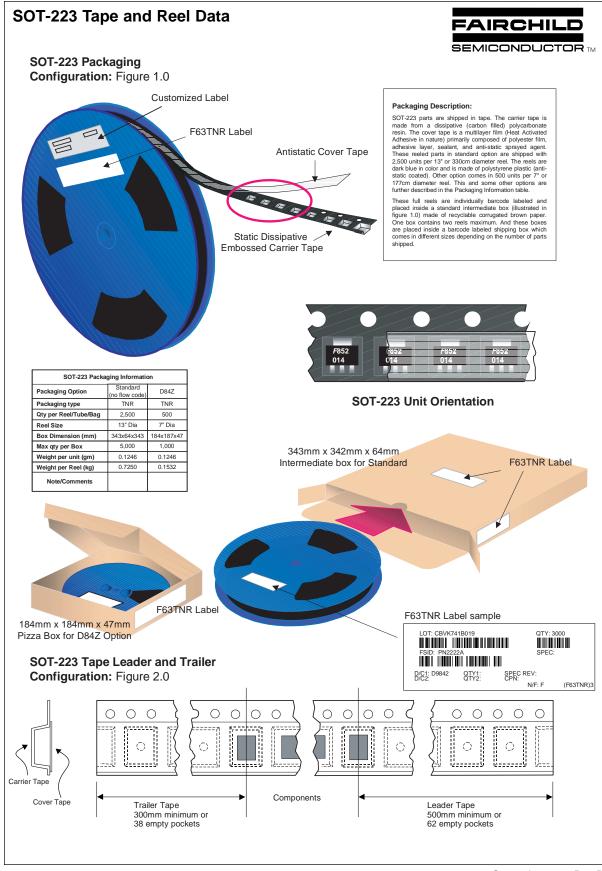
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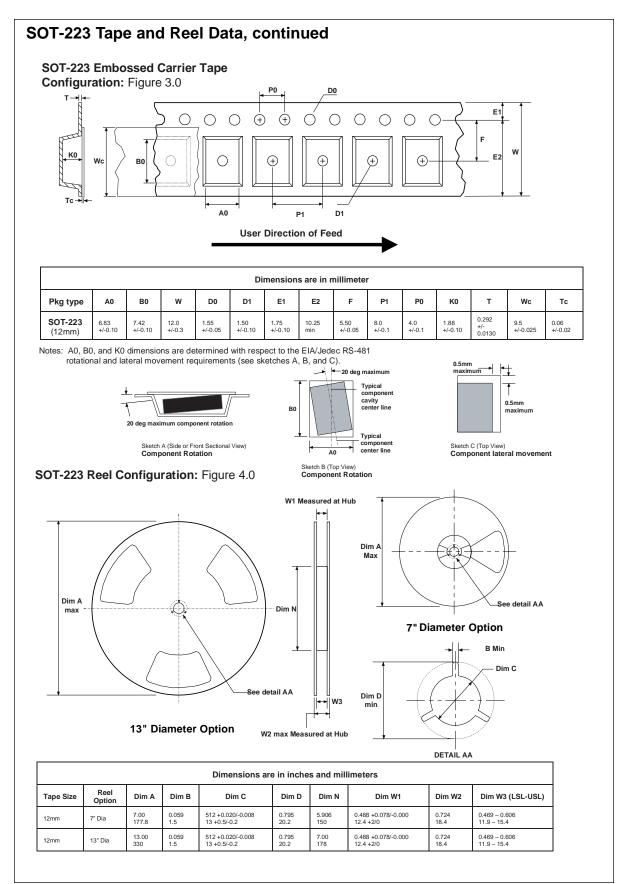
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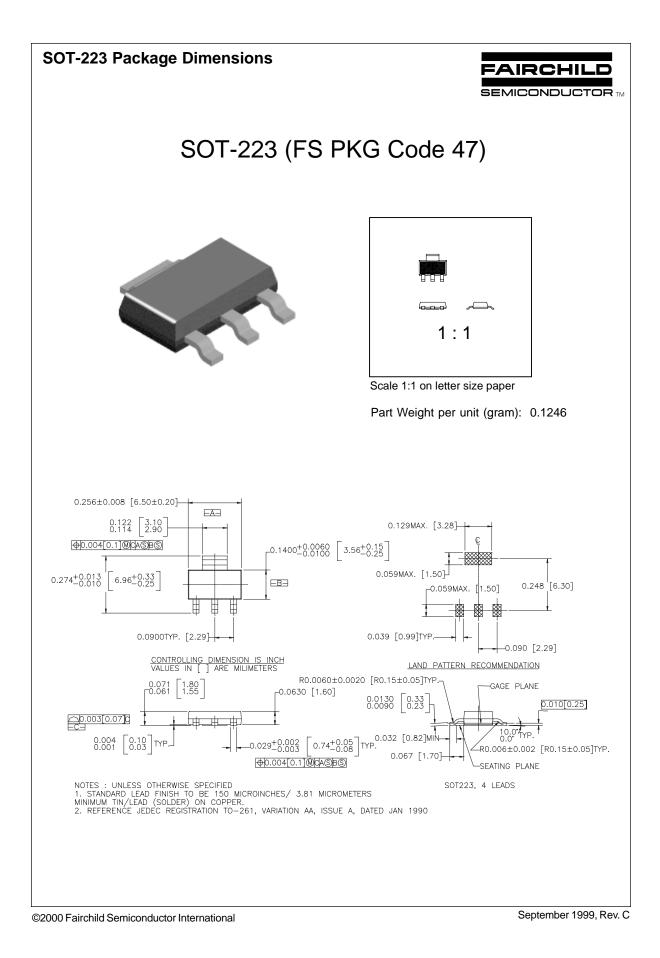


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